## AMENDMENT TO THE CLAIMS

- 1. (currently amended) An electrically programmable memory element, comprising:
  - a programmable resistance material;
- a threshold switching material comprising a chalcogen element; and
- a first layer of a dielectric material between said programmable resistance material and said threshold switching material, said dielectric material including silicon nitride.
- 2. (currently amended) The memory element of claim 1, further comprising a second layer of a dielectric material, said threshold switching material being between said first layer of said-dielectric material and said second layer of said dielectric material.
- 3. (currently amended) The memory element of claim 2, further comprising a third layer of a dielectric material, said programmable resistance material being between said third layer of said dielectric material and said first layer of said dielectric material.

- 4. (currently amended) The memory element of claim 1, further comprising a second layer of a dielectric material, said programmable resistance material being between said first layer of said dielectric material and said second layer of said-dielectric material.
- 5. (currently amended) The memory element of claim 1, wherein said programmable resistance material is a phase-change material.
- 6. (currently amended) The memory element of claim 1, wherein said programmable resistance material comprises a chalcogen element.

Claim 7 (canceled)

8. (currently amended) The memory element of claim 1, wherein said first layer of said dielectric material has a thickness of less than 100 Angstroms.

Claims 9-20 (cancelled).